

**Silicon PNP Power Transistors**

**2SA1887**

**DESCRIPTION**

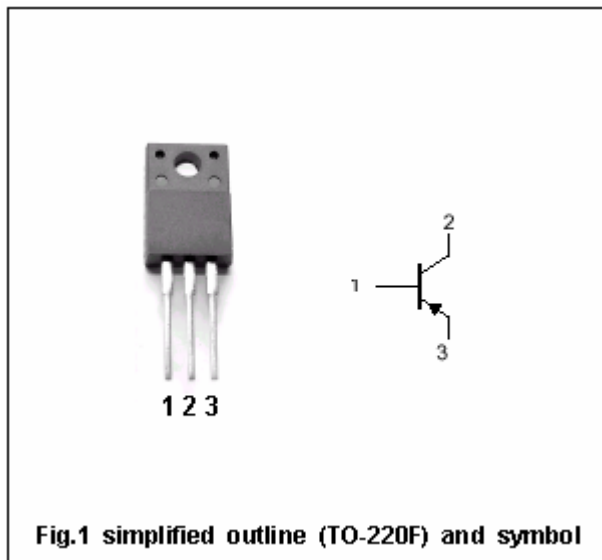
- With TO-220F package
- Low collector saturation voltage

**APPLICATIONS**

- High current switching applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



**Absolute maximum ratings (Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-80	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-50	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-7	V
I <sub>C</sub>	Collector current		-10	A
P <sub>C</sub>	Collector dissipation	T <sub>C</sub> =25	25	W
		T <sub>a</sub> =25	2.0	
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA ; I <sub>B</sub> =0	-50			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-5A ; I <sub>B</sub> =-0.25A		-0.2	-0.4	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-5A ; I <sub>B</sub> =-0.25A		-0.95	-1.4	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-70V ; I <sub>E</sub> =0			-1.0	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-7V ; I <sub>C</sub> =0			-1.0	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-1V	120		400	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V ; f=1MHz		215		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-1V		45		MHz

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PACKAGE OUTLINE

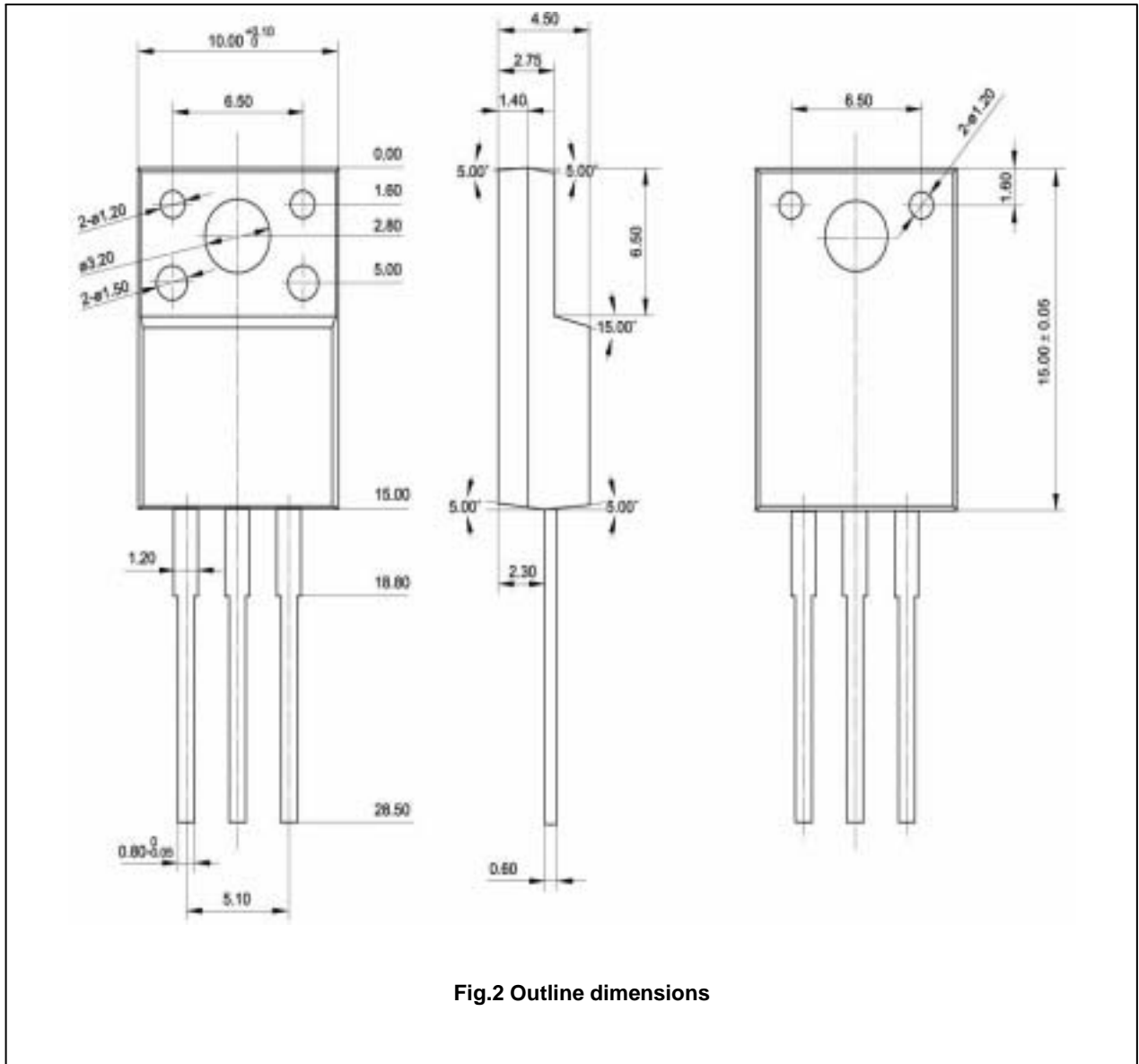


Fig.2 Outline dimensions